

# Schottky barrier diode

## RB521G-30

### ●Application

Rectifying small power

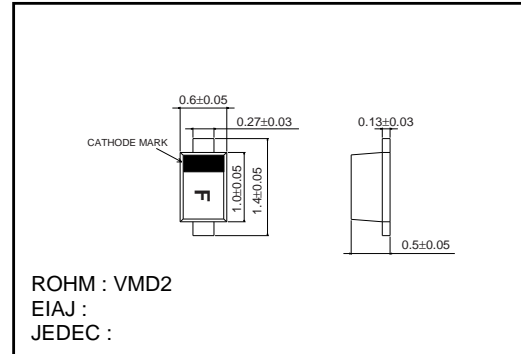
### ●Features

- 1) Ultra small mold type. (VMD2)
- 2) High reliability

### ●Construction

Silicon epitaxial planer

### ●External dimensions (Units : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (DC)	$V_R$	30	V
Average rectified forward current	$I_o$	100	mA
Forward current surge peak *	$I_{FSM}$	1	A
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40~+125	°C

\* 60Hz, 1cyc.

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.350	V	$I_F=10\text{mA}$
Reverse current	$I_R$	-	-	10	$\mu\text{A}$	$V_R=10\text{V}$

\* Please pay attention to static electricity when handling.

Diodes

●Electrical characteristic curves (Ta=25°C)

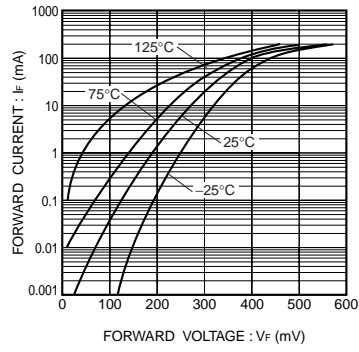


Fig.1 Forward characteristics

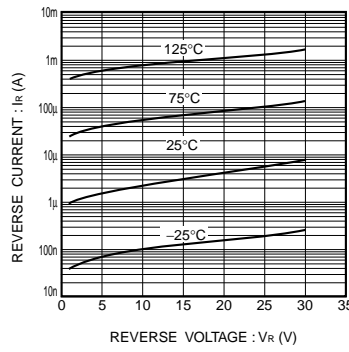


Fig.2 Reverse characteristics

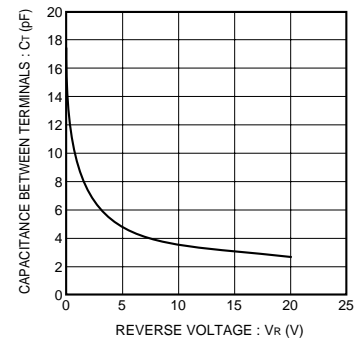


Fig.3 Capacitance between terminals characteristics